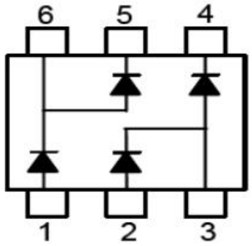
SOT-23-6L Switching Diode 开关二极管

■ Internal Configuration& Device Marking 内部结构与产品打标

Pin 管脚	 
Mark 打标	B34

■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Non-Repetitive Peak Reverse Voltages 不重复反向峰值电压	V_{RRM}	350	V
DC Reverse Voltage 直流反向电压	V_{RM}	300	V
RMS Reverse Voltage 反向电压均方根值	V_{RMS}	212	V
Forward Work Current 正向工作电流	$I_F(I_O)$	225	mA
Peak Forward Current 正向峰值电流	I_{FRM}	625	mA
Non-Repetitive Peak Surge Current 不重复峰值浪涌电流	I_{FSM}	1@t=1S	A
Power dissipation 耗散功率	P_D(Ta=25℃)	350	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	358	℃/W
Junction and Storage Temperature 结温和储藏温度	T_J,T_{stg}	-55to+150℃	

■Electrical Characteristics 电特性

(T$_A$=25℃ **unless otherwise noted** 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压(IR=150μA)	$V_{(BR)}$	350	—	—	V
Reverse Leakage Current(V_R=240V) 反向漏电流(V_R=240V,T_J=150℃)	I_R	—	20 0.5	100 100	nA μA
Forward Voltage(I_F=100mA) 正向电压(I_F=200mA)	V_F	—	0.95 1	1 1.25	V
Diode Capacitance 二极管电容(V_R=0V, f=1MHz)	C_D	—	2	5	pF
Reverse Recovery Time 反向恢复时间 I_{rr} = 0.1*I_R, R_L= 100Ω, I_F = 10 mA,V_R=6V	T_{rr}	—	—	50	nS

■Typical Characteristic Curve 典型特性曲线

Fig.1 Power Derating Curve

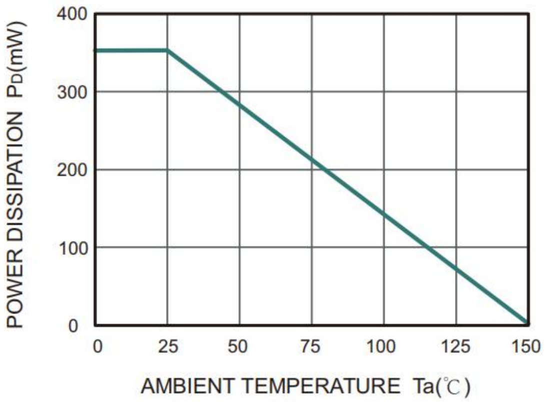


Fig.2 Reverse Characteristics

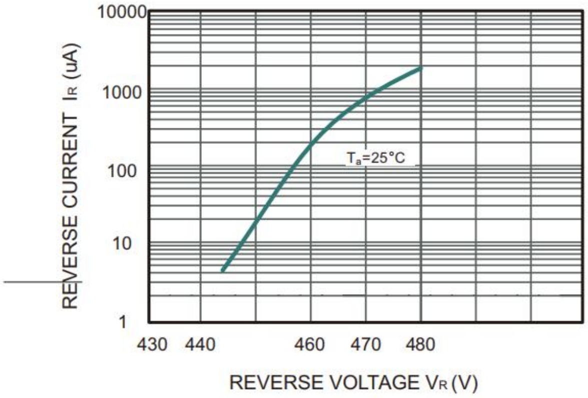


Fig.3 Forward Characteristics

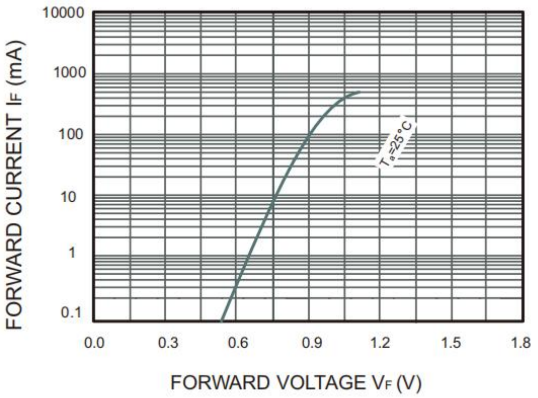


Fig.4 Capacitance Characteristics

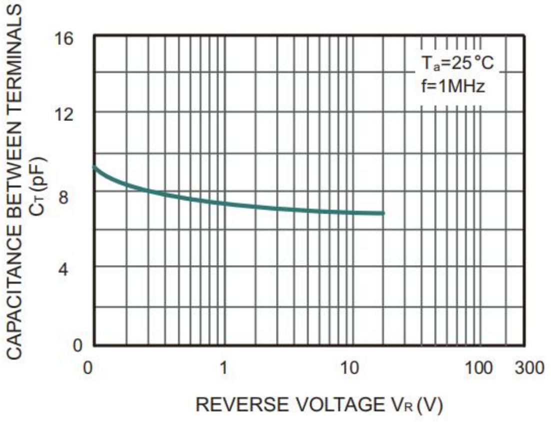
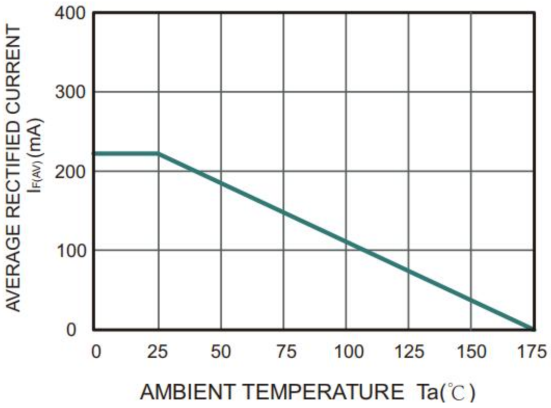
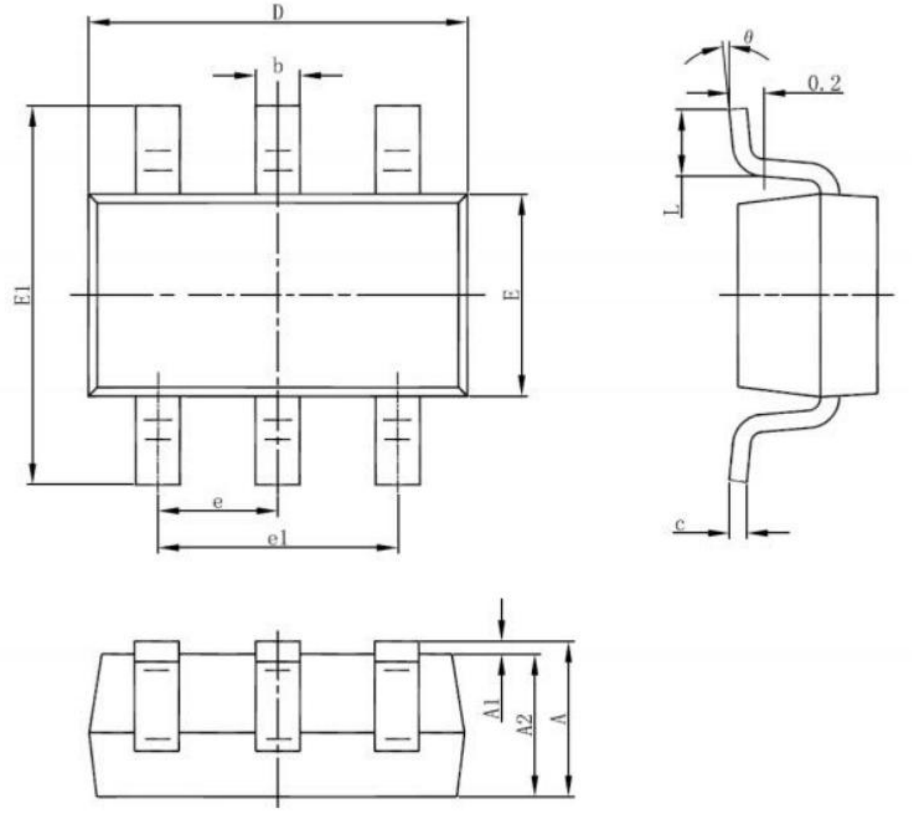


Fig.5 Semiconductor Intrinsic Property



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.900	1.00	0.035	0.039
e1	1.800	2.000	0.071	0.079
L	0.450	0.650	0.018	0.026
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°